Virtex-7 T and XT FPGAs Data Sheet: DC and AC Switching Characteristics

DS183 (v1.27) April 6, 2017 **Product Specification**

Introduction

Virtex®-7 T and XT FPGAs are available in -3, -2, -1, and -2L speed grades, with -3 having the highest performance. The -2L devices operate at V_{CCINT} = 1.0V and are screened for lower maximum static power. The speed specification of a -2L device is the same as the -2 speed grade. The -2G speed grade is available in devices utilizing Stacked Silicon Interconnect (SSI) technology. The -2G speed grade supports 12.5 Gb/s GTX or 13.1 Gb/s GTH transceivers as well as the standard -2 speed grade specifications.

Virtex-7 T and XT FPGA DC and AC characteristics are specified in commercial, extended, industrial, and military temperature ranges. Except for the operating temperature range or unless otherwise noted, all the DC and AC electrical parameters are the same for a particular speed grade (that is, the timing characteristics of a -1M speed grade military device are the same as for a -1C speed grade commercial device). However, only selected speed grades and/or devices are available in each temperature range.

All supply voltage and junction temperature specifications are representative of worst-case conditions. The parameters included are common to popular designs and typical applications.

Available device and package combinations can be found in:

- *7 Series FPGAs Overview* (DS180)
- *Defense-Grade 7 Series FPGAs Overview* (DS185)

This Virtex-7 T and XT FPGA data sheet, part of an overall set of documentation on the 7 series FPGAs, is available on the Xilinx website at www.xilinx.com/7.

DC Characteristics

Table 1: **Absolute Maximum Ratings(1)**

Symbol	Description	Min	Max	Units
FPGA Logic				
V_{CCINT}	Internal supply voltage	–0.5	1.1	V
V_{CCAUX}	Auxiliary supply voltage	–0.5	2.0	V
V_{CCBRAM}	Supply voltage for the block RAM memories	–0.5	1.1	V
V_{CCO}	Output drivers supply voltage for 3.3V HR I/O banks	–0.5	3.6	V
	Output drivers supply voltage for 1.8V HP I/O banks	–0.5	2.0	V
V_{CCAUX_IO}	Auxiliary supply voltage	–0.5	2.06	V
V_{REF}	Input reference voltage	–0.5	2.0	V
V_{IN}(2)(3)(4)	I/O input voltage for 3.3V HR I/O banks	–0.40	V_{CCO} + 0.55	V
	I/O input voltage for 1.8V HP I/O banks	–0.55	V_{CCO} + 0.55	V
	I/O input voltage (when V_{CCO} = 3.3V) for V_{REF} and differential I/O standards except TMDS_33(5)	–0.40	2.625	V
V_{CCBATT}	Key memory battery backup supply	–0.5	2.0	V
GTX and GTH Transceivers				
$V_{MGTAVCC}$	Analog supply voltage for the GTX/GTH transmitter and receiver circuits	–0.5	1.1	V
$V_{MGTAVTT}$	Analog supply voltage for the GTX/GTH transmitter and receiver termination circuits	–0.5	1.32	V
$V_{MGTVCCAUX}$	Auxiliary analog Quad PLL (QPLL) voltage supply for the GTX/GTH transceivers	–0.5	1.935	V
$V_{MGTREFCLK}$	GTX/GTH transceiver reference clock absolute input voltage	–0.5	1.32	V

Table 1: **Absolute Maximum Ratings[1] *(Cont'd)***

Symbol	Description	Min	Max	Units
$V_{MGTAVTTRCAL}$	Analog supply voltage for the resistor calibration circuit of the GTX/GTH transceiver column	–0.5	1.32	V
V_{IN}	Receiver (RXP/RXN) and Transmitter (TXP/TXN) absolute input voltage	–0.5	1.26	V
$I_{DCIN-FLOAT}$	DC input current for receiver input pins DC coupled RX termination = floating	–	14	mA
$I_{DCIN-MGTAVTT}$	DC input current for receiver input pins DC coupled RX termination = $V_{MGTAVTT}$	–	12	mA
$I_{DCIN-GND}$	DC input current for receiver input pins DC coupled RX termination = GND	–	6.5	mA
$I_{DCOUT-FLOAT}$	DC output current for transmitter pins DC coupled RX termination = floating	–	14	mA
$I_{DCOUT-MGTAVTT}$	DC output current for transmitter pins DC coupled RX termination = $V_{MGTAVTT}$	–	12	mA
XADC				
V_{CCADC}	XADC supply relative to GNDADC	–0.5	2.0	V
V_{REFP}	XADC reference input relative to GNDADC	–0.5	2.0	V
Temperature				
T_{STG}	Storage temperature (ambient)	–65	150	°C
T_{SOL}	Maximum soldering temperature for Pb/Sn component bodies[6]	–	+220	°C
	Maximum soldering temperature for Pb-free component bodies[6]	–	+260	°C
T_j	Maximum junction temperature[6]	–	+125	°C

Notes:

1. Stresses beyond those listed under Absolute Maximum Ratings might cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time might affect device reliability.
2. The lower absolute voltage specification always applies.
3. For I/O operation, refer to the *7 Series FPGAs SelectIO Resources User Guide* (UG471).
4. The maximum limit applies to DC signals. For maximum undershoot and overshoot AC specifications, see Table 4 and Table 5.
5. See Table 10 for TMDS_33 specifications.
6. For soldering guidelines and thermal considerations, see the *7 Series FPGA Packaging and Pinout Specification* (UG475).

Table 2: **Recommended Operating Conditions[1][2]**

Symbol	Description	Min	Typ	Max	Units
FPGA Logic					
V_{CCINT}[3]	Internal supply voltage	0.97	1.00	1.03	V
	Internal supply voltage for -1C devices with voltage identification (VID) bit programmed to run at 0.9V typical[4].	0.87	0.90	0.93	V
V_{CCBRAM}[3]	Block RAM supply voltage	0.97	1.00	1.03	V
	Block RAM supply voltage for -1C devices with voltage identification (VID) bit programmed to run at 0.9V typical[4].	0.87	0.90	1.03	V
V_{CCAUX}	Auxiliary supply voltage	1.71	1.80	1.89	V
V_{CCO}[5][6]	Supply voltage for 3.3V HR I/O banks	1.14	–	3.465	V
	Supply voltage for 1.8V HP I/O banks	1.14	–	1.89	V
V_{CCAUX_IO}[7]	Auxiliary supply voltage when set to 1.8V	1.71	1.80	1.89	V
	Auxiliary supply voltage when set to 2.0V	1.94	2.00	2.06	V
V_{IN}[8]	I/O input voltage	–0.20	–	V_{CCO} + 0.2	V
	I/O input voltage (when V_{CCO} = 3.3V) for V_{REF} and differential I/O standards except TMDS_33[9]	–0.20	–	2.625	V
I_{IN}[10]	Maximum current through any pin in a powered or unpowered bank when forward biasing the clamp diode.	–	–	10	mA

Table 2: **Recommended Operating Conditions[1][2] *(Cont'd)***

Symbol	Description	Min	Typ	Max	Units
V_{CCBATT}[11]	Battery voltage	1.0	–	1.89	V
GTX and GTH Transceivers					
$V_{MGTAVCC}$[12]	Analog supply voltage for the GTX/GTH transceiver QPLL frequency range ≤ 10.3125 GHz[13][14]	0.97	1.0	1.08	V
	Analog supply voltage for the GTX/GTH transceiver QPLL frequency range > 10.3125 GHz	1.02	1.05	1.08	V
$V_{MGTAVTT}$[12]	Analog supply voltage for the GTX/GTH transmitter and receiver termination circuits	1.17	1.2	1.23	V
$V_{MGTVCCAUX}$[12]	Auxiliary analog Quad PLL (QPLL) voltage supply for the transceivers	1.75	1.80	1.85	V
$V_{MGTAVTTRCAL}$[12]	Analog supply voltage for the resistor calibration circuit of the GTX/GTH transceiver column	1.17	1.2	1.23	V
XADC					
V_{CCADC}	XADC supply relative to GNDADC	1.71	1.80	1.89	V
V_{REFP}	Externally supplied reference voltage	1.20	1.25	1.30	V
Temperature					
T_j	Junction temperature operating range for commercial (C) temperature devices	0	–	85	°C
	Junction temperature operating range for extended (E) temperature devices	0	–	100	°C
	Junction temperature operating range for industrial (I) temperature devices	–40	–	100	°C
	Junction temperature operating range for military (M) temperature devices	–55	–	125	°C

Notes:

1. All voltages are relative to ground.
2. For the design of the power distribution system, consult the *7 Series FPGAs PCB Design and Pin Planning Guide* (UG483).
3. V_{CCINT} and V_{CCBRAM} should be connected to the same supply.
4. For more information on the VID bit see the *Lowering Power using the Voltage Identification Bit* application note (XAPP555).
5. Configuration data is retained even if V_{CCO} drops to 0V.
6. Includes V_{CCO} of 1.2V, 1.35V, 1.5V, 1.8V, 2.5V (HR I/O only), 3.3V (HR I/O only) at ±5%.
7. For more information, refer to the V_{CCAUX_IO} section of *7 Series FPGAs SelectIO Resources User Guide* (UG471).
8. The lower absolute voltage specification always applies.
9. See Table 10 for TMDS_33 specifications.
10. A total of 200 mA per bank should not be exceeded.
11. V_{CCBATT} is required only when using bitstream encryption. If battery is not used, connect V_{CCBATT} to either ground or V_{CCAUX}.
12. Each voltage listed requires the filter circuit described in the *7 Series FPGAs GTX/GTH Transceiver User Guide* (UG476).
13. For data rates ≤ 10.3125 Gb/s, $V_{MGTAVCC}$ should be 1.0V ±3% for lower power consumption.
14. For lower power consumption, $V_{MGTAVCC}$ should be 1.0V ±3% over the entire CPLL frequency range.

Table 3: **DC Characteristics Over Recommended Operating Conditions**

Symbol	Description	Min	Typ[1]	Max	Units
V_{DRINT}	Data retention V_{CCINT} voltage (below which configuration data might be lost)	0.75	–	–	V
V_{DRI}	Data retention V_{CCAUX} voltage (below which configuration data might be lost)	1.5	–	–	V
I_{REF}	V_{REF} leakage current per pin	–	–	15	µA
I_L	Input or output leakage current per pin (sample-tested)	–	–	15	µA
C_{IN}[2]	Die input capacitance at the pad	–	–	8	pF

Table 3: **DC Characteristics Over Recommended Operating Conditions *(Cont'd)***

Symbol	Description	Min	Typ(1)	Max	Units
I_{RPU}	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 3.3V	90	–	330	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 2.5V	68	–	250	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.8V	34	–	220	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.5V	23	–	150	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.2V	12	–	120	µA
I_{RPD}	Pad pull-down (when selected) @ V_{IN} = 3.3V	68	–	330	µA
	Pad pull-down (when selected) @ V_{IN} = 1.8V	45	–	180	µA
I_{CCADC}	Analog supply current, analog circuits in powered up state	–	–	25	mA
I_{BATT}(3)	Battery supply current	–	–	150	nA
R_{IN_TERM}(4)	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 (UNTUNED_SPLIT_40)	28	40	55	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 (UNTUNED_SPLIT_50)	35	50	65	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 (UNTUNED_SPLIT_60)	44	60	83	Ω
n	Temperature diode ideality factor	–	1.010	–	–
r	Temperature diode series resistance	–	2	–	Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. This measurement represents the die capacitance at the pad, not including the package.
3. Maximum value specified for worst case process at 25°C.
4. Termination resistance to a V_{CCO}/2 level.

Table 4: **V_{IN} Maximum Allowed AC Voltage Overshoot and Undershoot for 3.3V HR I/O Banks(1)(2)**

AC Voltage Overshoot	% of UI @–55°C to 125°C	AC Voltage Undershoot	% of UI @–55°C to 125°C
V_{CCO} + 0.55	100	–0.40	100
		–0.45	61.7
		–0.50	25.8
		–0.55	11.0
V_{CCO} + 0.60	46.6	–0.60	4.77
V_{CCO} + 0.65	21.2	–0.65	2.10
V_{CCO} + 0.70	9.75	–0.70	0.94
V_{CCO} + 0.75	4.55	–0.75	0.43
V_{CCO} + 0.80	2.15	–0.80	0.20
V_{CCO} + 0.85	1.02	–0.85	0.09
V_{CCO} + 0.90	0.49	–0.90	0.04
V_{CCO} + 0.95	0.24	–0.95	0.02

Notes:

1. A total of 200 mA per bank should not be exceeded.
2. The peak voltage of the overshoot or undershoot, and the duration above V_{CCO} + 0.20V or below GND – 0.20V, must not exceed the values in this table.

Table 5: **V_{IN} Maximum Allowed AC Voltage Overshoot and Undershoot for 1.8V HP I/O Banks(1)(2)**

AC Voltage Overshoot	% of UI @–55°C to 125°C	AC Voltage Undershoot	% of UI @–55°C to 125°C
V_{CCO} + 0.55	100	–0.55	100
V_{CCO} + 0.60	50.0(3)	–0.60	50.0(3)
V_{CCO} + 0.65	50.0(3)	–0.65	50.0(3)
V_{CCO} + 0.70	47.0	–0.70	50.0(3)
V_{CCO} + 0.75	21.2	–0.75	50.0(3)
V_{CCO} + 0.80	9.71	–0.80	50.0(3)
V_{CCO} + 0.85	4.51	–0.85	28.4
V_{CCO} + 0.90	2.12	–0.90	12.7
V_{CCO} + 0.95	1.01	–0.95	5.79

Notes:

1. A total of 200 mA per bank should not be exceeded.
2. The peak voltage of the overshoot or undershoot, and the duration above V_{CCO} + 0.20V or below GND – 0.20V, must not exceed the values in this table.
3. For UI lasting less than 20 µs.

Table 6: **Typical Quiescent Supply Current**

Symbol	Description	Device	Speed Grade						Units
			-3	-2G	-2	-2L	-1	-1M	
I_{CCINTQ}	Quiescent V_{CCINT} supply current	XC7V585T	1483	1483	1483	1483	1483	N/A	mA
		XC7V2000T	N/A	3756	3756	3756	3756	N/A	mA
		XC7VX330T	1012	1012	1012	1012	1012	N/A	mA
		XC7VX415T	1324	1324	1324	1324	1324	N/A	mA
		XC7VX485T	1578	1578	1578	1578	1578	N/A	mA
		XC7VX550T	2214	2214	2214	2214	2214	N/A	mA
		XC7VX690T	2214	2214	2214	2214	2214	N/A	mA
		XC7VX980T	N/A	2580	2580	2580	2580	N/A	mA
		XC7VX1140T	N/A	3448	3448	3448	3448	N/A	mA
		XQ7V585T	N/A	N/A	1483	1483	1483	1483	mA
		XQ7VX330T	N/A	N/A	1012	1012	1012	1012	mA
		XQ7VX485T	N/A	N/A	1578	1578	1578	1578	mA
		XQ7VX690T	N/A	N/A	2214	N/A	2214	N/A	mA
		XQ7VX980T	N/A	N/A	N/A	2580	2580	N/A	mA

Table 6: **Typical Quiescent Supply Current *(Cont'd)***

Symbol	Description	Device	Speed Grade						Units
			-3	-2G	-2	-2L	-1	-1M	
I_{CCOQ}	Quiescent V_{CCO} supply current	XC7V585T	1	1	1	1	1	N/A	mA
		XC7V2000T	N/A	1	1	1	1	N/A	mA
		XC7VX330T	1	1	1	1	1	N/A	mA
		XC7VX415T	1	1	1	1	1	N/A	mA
		XC7VX485T	1	1	1	1	1	N/A	mA
		XC7VX550T	1	1	1	1	1	N/A	mA
		XC7VX690T	1	1	1	1	1	N/A	mA
		XC7VX980T	N/A	1	1	1	1	N/A	mA
		XC7VX1140T	N/A	1	1	1	1	N/A	mA
		XQ7V585T	N/A	N/A	1	1	1	1	mA
		XQ7VX330T	N/A	N/A	1	1	1	1	mA
		XQ7VX485T	N/A	N/A	1	1	1	1	mA
		XQ7VX690T	N/A	N/A	1	N/A	1	N/A	mA
		XQ7VX980T	N/A	N/A	N/A	1	1	N/A	mA
I_{CCAUXQ}	Quiescent V_{CCAUX} supply current	XC7V585T	114	114	114	114	114	N/A	mA
		XC7V2000T	N/A	315	315	315	315	N/A	mA
		XC7VX330T	73	73	73	73	73	N/A	mA
		XC7VX415T	88	88	88	88	88	N/A	mA
		XC7VX485T	104	104	104	104	104	N/A	mA
		XC7VX550T	147	147	147	147	147	N/A	mA
		XC7VX690T	147	147	147	147	147	N/A	mA
		XC7VX980T	N/A	183	183	183	183	N/A	mA
		XC7VX1140T	N/A	250	250	250	250	N/A	mA
		XQ7V585T	N/A	N/A	114	114	114	114	mA
		XQ7VX330T	N/A	N/A	73	73	73	73	mA
		XQ7VX485T	N/A	N/A	104	104	104	104	mA
		XQ7VX690T	N/A	N/A	147	N/A	147	N/A	mA
		XQ7VX980T	N/A	N/A	N/A	183	183	N/A	mA

Table 6: **Typical Quiescent Supply Current *(Cont'd)***

Symbol	Description	Device	Speed Grade						Units
			-3	-2G	-2	-2L	-1	-1M	
I_{CCAUX_IOQ}	Quiescent V_{CCAUX_IO} supply current	XC7V585T	2	2	2	2	2	N/A	mA
		XC7V2000T	N/A	2	2	2	2	N/A	mA
		XC7VX330T	2	2	2	2	2	N/A	mA
		XC7VX415T	2	2	2	2	2	N/A	mA
		XC7VX485T	2	2	2	2	2	N/A	mA
		XC7VX550T	2	2	2	2	2	N/A	mA
		XC7VX690T	2	2	2	2	2	N/A	mA
		XC7VX980T	N/A	2	2	2	2	N/A	mA
		XC7VX1140T	N/A	2	2	2	2	N/A	mA
		XQ7V585T	N/A	N/A	2	2	2	2	mA
		XQ7VX330T	N/A	N/A	2	2	2	2	mA
		XQ7VX485T	N/A	N/A	2	2	2	2	mA
		XQ7VX690T	N/A	N/A	2	N/A	2	N/A	mA
		XQ7VX980T	N/A	N/A	N/A	2	2	N/A	mA
$I_{CCBRAMQ}$	Quiescent V_{CCBRAM} supply current	XC7V585T	34	34	34	34	34	N/A	mA
		XC7V2000T	N/A	56	56	56	56	N/A	mA
		XC7VX330T	32	32	32	32	32	N/A	mA
		XC7VX415T	38	38	38	38	38	N/A	mA
		XC7VX485T	44	44	44	44	44	N/A	mA
		XC7VX550T	63	63	63	63	63	N/A	mA
		XC7VX690T	63	63	63	63	63	N/A	mA
		XC7VX980T	N/A	65	65	65	65	N/A	mA
		XC7VX1140T	N/A	81	81	81	81	N/A	mA
		XQ7V585T	N/A	N/A	34	34	34	34	mA
		XQ7VX330T	N/A	N/A	32	32	32	32	mA
		XQ7VX485T	N/A	N/A	44	44	44	44	mA
		XQ7VX690T	N/A	N/A	63	N/A	63	N/A	mA
		XQ7VX980T	N/A	N/A	N/A	65	65	N/A	mA

Notes:

1. Typical values are specified at nominal voltage, 85°C junction temperatures (T_j) with single-ended SelectIO resources.
2. Typical values are for blank configured devices with no output current loads, no active input pull-up resistors, all I/O pins are 3-state and floating.
3. Use the Xilinx Power Estimator (XPE) spreadsheet tool (download at http://www.xilinx.com/power) to estimate static power consumption for conditions other than those specified.

Power-On/Off Power Supply Sequencing

The recommended power-on sequence is V_{CCINT}, V_{CCBRAM}, V_{CCAUX}, V_{CCAUX_IO}, and V_{CCO} to achieve minimum current draw and ensure that the I/Os are 3-stated at power-on. The recommended power-off sequence is the reverse of the power-on sequence. If V_{CCINT} and V_{CCBRAM} have the same recommended voltage levels then both can be powered by the same supply and ramped simultaneously. If V_{CCAUX}, V_{CCAUX_IO}, and V_{CCO} have the same recommended voltage levels then they can be powered by the same supply and ramped simultaneously.

For V_{CCO} voltages of 3.3V in HR I/O banks and configuration bank 0:

- The voltage difference between V_{CCO} and V_{CCAUX} must not exceed 2.625V for longer than $T_{VCCO2VCCAUX}$ for each power-on/off cycle to maintain device reliability levels.
- The $T_{VCCO2VCCAUX}$ time can be allocated in any percentage between the power-on and power-off ramps.

The recommended power-on sequence to achieve minimum current draw for the GTX/GTH transceivers is V_{CCINT}, $V_{MGTAVCC}$, $V_{MGTAVTT}$ OR $V_{MGTAVCC}$, V_{CCINT}, $V_{MGTAVTT}$. There is no recommended sequencing for $V_{MGTVCCAUX}$. Both $V_{MGTAVCC}$ and V_{CCINT} can be ramped simultaneously. The recommended power-off sequence is the reverse of the power-on sequence to achieve minimum current draw.

If these recommended sequences are not met, current drawn from $V_{MGTAVTT}$ can be higher than specifications during power-up and power-down.

- When $V_{MGTAVTT}$ is powered before $V_{MGTAVCC}$ and $V_{MGTAVTT} - V_{MGTAVCC} > 150$ mV and $V_{MGTAVCC} < 0.7$V, the $V_{MGTAVTT}$ current draw can increase by 460 mA per transceiver during $V_{MGTAVCC}$ ramp up. The duration of the current draw can be up to 0.3 x $T_{MGTAVCC}$ (ramp time from GND to 90% of $V_{MGTAVCC}$). The reverse is true for power-down.
- When $V_{MGTAVTT}$ is powered before V_{CCINT} and $V_{MGTAVTT} - V_{CCINT} > 150$ mV and $V_{CCINT} < 0.7$V, the $V_{MGTAVTT}$ current draw can increase by 50 mA per transceiver during V_{CCINT} ramp up. The duration of the current draw can be up to 0.3 x T_{VCCINT} (ramp time from GND to 90% of V_{CCINT}). The reverse is true for power-down.

There is no recommended sequence for supplies not shown.

Table 7 shows the minimum current, in addition to I_{CCQ}, that is required by Virtex-7 T and XT devices for proper power-on and configuration. If the current minimums shown in Table 6 and Table 7 are met, the device powers on after all five supplies have passed through their power-on reset threshold voltages. The FPGA must not be configured until after V_{CCINT} is applied.

Once initialized and configured, use the Xilinx Power tools to estimate current drain on these supplies.

Table 7: **Power-On Current for Virtex-7 T and XT Devices**

Device	$I_{CCINTMIN}$	$I_{CCAUXMIN}$	I_{CCOMIN}	I_{CCAUX_IO}	I_{CCBRAM}	Units
XC7V585T	I_{CCINTQ} + 2700	I_{CCAUXQ} + 40	I_{CCOQ} + 60 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 108	mA
XC7V2000T	I_{CCINTQ} + 4000	I_{CCAUXQ} + 80	I_{CCOQ} + 60 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 176	mA
XC7VX330T	I_{CCINTQ} + 1000	I_{CCAUXQ} + 65	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 95	mA
XC7VX415T	I_{CCINTQ} + 1200	I_{CCAUXQ} + 75	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 115	mA
XC7VX485T	I_{CCINTQ} + 1200	I_{CCAUXQ} + 80	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 140	mA
XC7VX550T	I_{CCINTQ} + 3300	I_{CCAUXQ} + 143	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 57 mA per bank	$I_{CCBRAMQ}$ + 200	mA
XC7VX690T	I_{CCINTQ} + 3300	I_{CCAUXQ} + 143	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 57 mA per bank	$I_{CCBRAMQ}$ + 200	mA
XC7VX980T	I_{CCINTQ} + 6500	I_{CCAUXQ} + 202	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 60 mA per bank	$I_{CCBRAMQ}$ + 204	mA
XC7VX1140T	I_{CCINTQ} + 8000	I_{CCAUXQ} + 235	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 63 mA per bank	$I_{CCBRAMQ}$ + 256	mA
XQ7V585T	I_{CCINTQ} + 2700	I_{CCAUXQ} + 40	I_{CCOQ} + 60 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 108	mA
XQ7VX330T	I_{CCINTQ} + 1000	I_{CCAUXQ} + 65	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 95	mA
XQ7VX485T	I_{CCINTQ} + 1200	I_{CCAUXQ} + 80	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 140	mA
XQ7VX690T	I_{CCINTQ} + 3300	I_{CCAUXQ} + 143	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 57 mA per bank	$I_{CCBRAMQ}$ + 200	mA
XQ7VX980T	I_{CCINTQ} + 6500	I_{CCAUXQ} + 202	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 60 mA per bank	$I_{CCBRAMQ}$ + 204	mA

Table 8: **Power Supply Ramp Time**

Symbol	Description	Conditions	Min	Max	Units
T_{VCCINT}	Ramp time from GND to 90% of V_{CCINT}		0.2	50	ms
T_{VCCO}	Ramp time from GND to 90% of V_{CCO}		0.2	50	ms
T_{VCCAUX}	Ramp time from GND to 90% of V_{CCAUX}		0.2	50	ms
T_{VCCAUX_IO}	Ramp time from GND to 90% of V_{CCAUX_IO}		0.2	50	ms
$T_{VCCBRAM}$	Ramp time from GND to 90% of V_{CCBRAM}		0.2	50	ms
$T_{VCCO2VCCAUX}$	Allowed time per power cycle for $V_{CCO} - V_{CCAUX} > 2.625V$	$T_J = 125°C$(1)	–	300	ms
		$T_J = 100°C$(1)	–	500	
		$T_J = 85°C$(1)	–	800	
$T_{MGTAVCC}$	Ramp time from GND to 90% of $V_{MGTAVCC}$		0.2	50	ms
$T_{MGTAVTT}$	Ramp time from GND to 90% of $V_{MGTAVTT}$		0.2	50	ms
$T_{MGTVCCAUX}$	Ramp time from GND to 90% of $V_{MGTVCCAUX}$		0.2	50	ms

Notes:

1. Based on 240,000 power cycles with nominal V_{CCO} of 3.3V or 36,500 power cycles with a worst case V_{CCO} of 3.465V.

DC Input and Output Levels

Values for V_{IL} and V_{IH} are recommended input voltages. Values for I_{OL} and I_{OH} are guaranteed over the recommended operating conditions at the V_{OL} and V_{OH} test points. Only selected standards are tested. These are chosen to ensure that all standards meet their specifications. The selected standards are tested at a minimum V_{CCO} with the respective V_{OL} and V_{OH} voltage levels shown. Other standards are sample tested.

Table 9: **SelectIO DC Input and Output Levels**(1)(2)

I/O Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
HSTL_I	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	8	–8
HSTL_I_12	–0.300	V_{REF} – 0.080	V_{REF} + 0.080	V_{CCO} + 0.300	25% V_{CCO}	75% V_{CCO}	6.3	–6.3
HSTL_I_18	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	8	–8
HSTL_II	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	16	–16
HSTL_II_18	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	16	–16
HSUL_12	–0.300	V_{REF} – 0.130	V_{REF} + 0.130	V_{CCO} + 0.300	20% V_{CCO}	80% V_{CCO}	0.1	–0.1
LVCMOS12	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	Note 3	Note 3
LVCMOS15, LVDCI_15	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	25% V_{CCO}	75% V_{CCO}	Note 4	Note 4
LVCMOS18, LVDCI_18	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} – 0.450	Note 5	Note 5
LVCMOS25	–0.300	0.700	1.700	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	Note 6	Note 6
LVCMOS33	–0.300	0.800	2.000	3.450	0.400	V_{CCO} – 0.400	Note 6	Note 6
LVTTL	–0.300	0.800	2.000	3.450	0.400	2.400	Note 7	Note 7
MOBILE_DDR	–0.300	20% V_{CCO}	80% V_{CCO}	V_{CCO} + 0.300	10% V_{CCO}	90% V_{CCO}	0.1	–0.1
PCI33_3	–0.400	30% V_{CCO}	50% V_{CCO}	V_{CCO} + 0.500	10% V_{CCO}	90% V_{CCO}	1.5	–0.5
SSTL12	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	14.25	–14.25
SSTL135	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	13.0	–13.0
SSTL135_R	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	8.9	–8.9
SSTL15	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.175	V_{CCO}/2 + 0.175	13.0	–13.0
SSTL15_R	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.175	V_{CCO}/2 + 0.175	8.9	–8.9
SSTL18_I	–0.300	V_{REF} – 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	V_{CCO}/2 – 0.470	V_{CCO}/2 + 0.470	8	–8
SSTL18_II	–0.300	V_{REF} – 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	V_{CCO}/2 – 0.600	V_{CCO}/2 + 0.600	13.4	–13.4

Notes:

1. Tested according to relevant specifications.
2. 3.3V and 2.5V standards are only supported in 3.3V I/O banks.
3. Supported drive strengths of 2, 4, 6, or 8 mA in HP I/O banks and 4, 8, or 12 mA in HR I/O banks.
4. Supported drive strengths of 2, 4, 6, 8, 12, or 16 mA in HP I/O banks and 4, 8, 12, or 16 mA in HR I/O banks.
5. Supported drive strengths of 2, 4, 6, 8, 12, or 16 mA in HP I/O banks and 4, 8, 12, 16, or 24 mA in HR I/O banks.
6. Supported drive strengths of 4, 8, 12, or 16 mA
7. Supported drive strengths of 4, 8, 12, 16, or 24 mA
8. For detailed interface specific DC voltage levels, see the *7 Series FPGAs SelectIO Resources User Guide* (UG471).